

ISC Silicon NPN Power Transistor

2SD726

DESCRIPTION

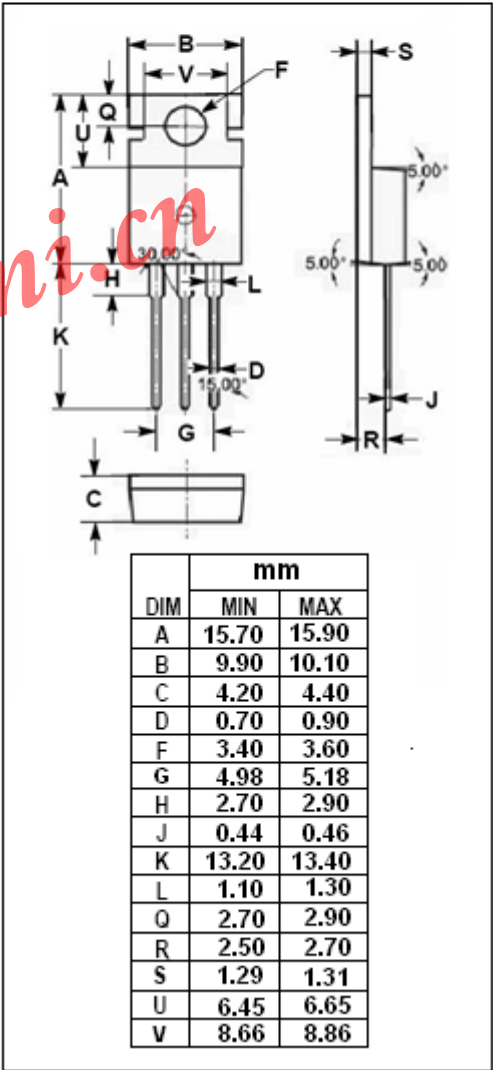
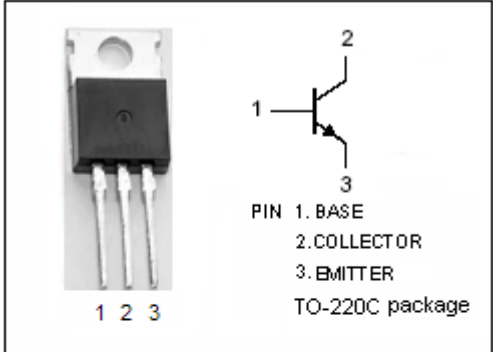
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 80V(\text{Min})$
- High Power Dissipation
- Complement to Type 2SB690

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Collector Current-Peak	8	A
P_C	Total Power Dissipation @ $T_C=25^{\circ}\text{C}$	40	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-45~150	$^{\circ}\text{C}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}$; $R_{BE}=\infty$	80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=10\mu\text{A}$; $I_C=0$	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2\text{A}$; $I_B=0.2\text{A}$			2.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=1\text{A}$; $V_{CE}=5\text{V}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=80\text{V}$; $I_E=0$			0.1	mA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}$; $V_{CE}=5\text{V}$	60		200	
h_{FE-2}	DC Current Gain	$I_C=0.1\text{A}$; $V_{CE}=5\text{V}$	35			
C_{OB}	Collector Output Capacitance	$I_E=0$; $V_{CB}=20\text{V}$; $f=1\text{MHz}$		40		pF
f_T	Current-Gain—Bandwidth Product	$I_C=0.5\text{A}$; $V_{CE}=5\text{V}$		10		MHz

◆ h_{FE-1} Classifications

B	C
60-120	100-200